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**INFORMATION DISCLOSURE
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(Use several sheets if necessary)APPLICANT
Aaron Scott Lukas, et al.

FILING DATE

GROUP

(37 CFR 1.98(b))

U.S. PATENT DOCUMENTS

| EXAM- INER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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| | | | | | YES | NO |
| WO 9 7 0 0 5 3 5 | | World | | | X | |
| WO 02 0 6 5 5 3 4 | | World | | | X | |
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| | A. Guo, et al., "Highly Active Visible-Light Photocatalysts for Curing a Ceramic Precursor ¹ ," Chem Mater. 10, pp. 531-536 (1998). |
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EXAMINER

DATE CONSIDERED

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.